



# BSS84KEJ

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## P-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$	-60 V
$I_D$	-0.26 A
$R_{DS(ON)}$ ( at $V_{GS}=-10V$ )	3
$R_{DS(ON)}$ ( at $V_{GS}=-4.5V$ )	3.5
Gate-Source ESD Rating Up to 2KV (HBM)	



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## Typical Electrical and Thermal Characteristics Diagrams

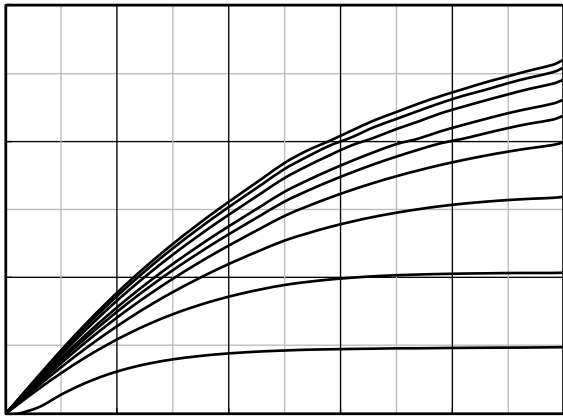


Figure 1. Output Characteristics

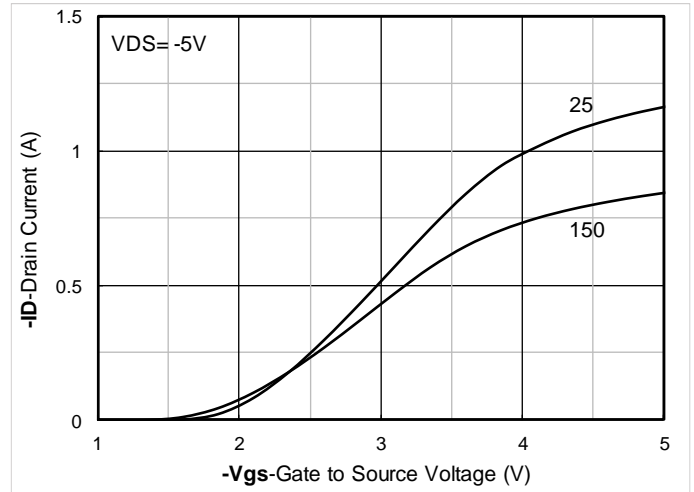


Figure 2. Transfer Characteristics



Figure 3. Capacitance Characteristics

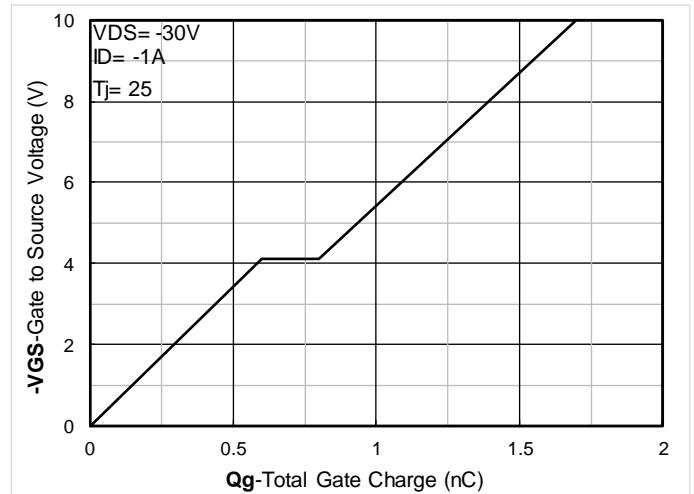


Figure 4. Gate Charge

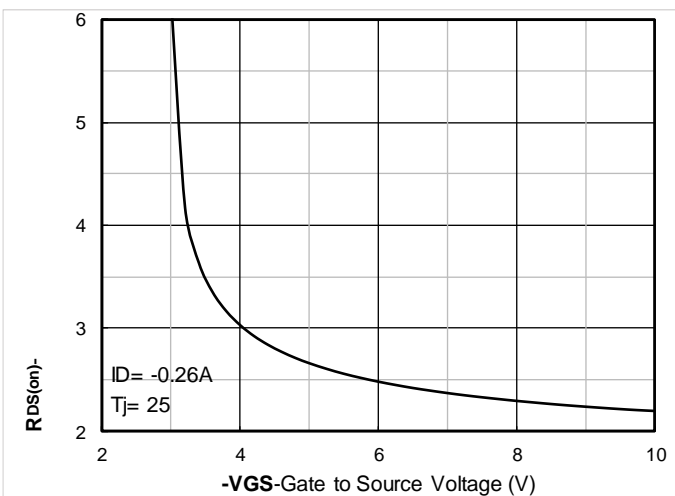


Figure 5. On-Resistance vs Gate to Source Voltage

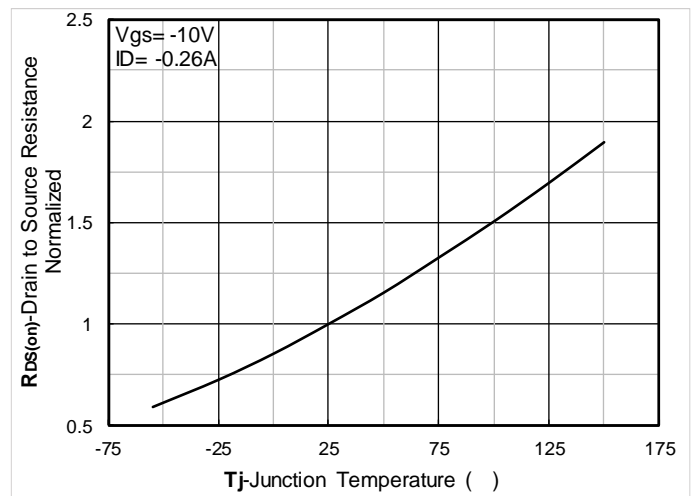


Figure 6. Normalized On-Resistance



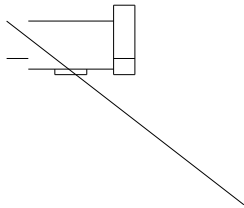
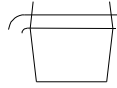
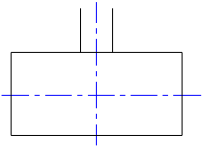


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area



SOT-523 Package information





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## Disclaimer

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